

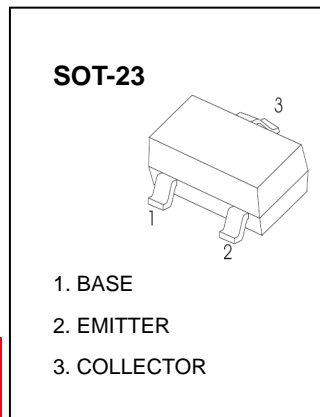


SOT-23 Plastic-Encapsulate Transistors

A1015 TRANSISTOR (PNP)

FEATURES

- High voltage and high current
- Excellent h_{FE} Linearity
- Low noise
- Complementary to C1815



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MARKING: BA

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-50	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	150	mA
P _C	Collector Power Dissipation	200	mW
T _J	Junction Temperature	125	°C
T _{stg}	Storage Temperature	-55-125	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = -100u A, I _E =0	-50			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -0.1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100 u A, I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-50V, I _E =0			-0.1	u A
Collector cut-off current	I _{CEO}	V _{CE} = -50V, I _B =0			-0.1	u A
Emitter cut-off current	I _{EBO}	V _{EB} =- 5V, I _C =0			-0.1	u A
DC current gain	h _{FE}	V _{CE} =-6V, I _C = -2mA	130		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100 mA, I _B = -10mA			-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100 mA, I _B = -10mA			-1.1	V
Transition frequency	f _T	V _{CE} =-10V, I _C = -1mA f=30MHz	80			MHz

CLASSIFICATION OF h_{FE}

Rank	L	H
Range	130-200	200-400